

# Advanced CMOS TTL Input – 74ACT32

#### Quad 2-Input OR Gate with LSTTL compatible inputs in bare die form

Rev 1.1 08/11/2022

### Description

The 74ACT32 quad 2-input OR gate is produced on a 1.5µm 5V CMOS process and provides four independent 2-input OR gates with standard push-pull outputs. The device gates perform the Boolean function  $Y = \overline{A} \cdot \overline{B}$  or Y = A + B. Device inputs directly accept LSTTL or CMOS. All inputs are protected against ESD and excess voltage transients. This device is designed specifically to interface both Bipolar Logic and High Speed CMOS systems.

### Features:

- Inputs directly accept TTL
- Outputs directly interface CMOS, NMOS and TTL
- Outputs Source/Sink 24 mA
- Low Input Current: 1µA
- Functionally compatible with bipolar 74F32
- Lower power alternative to bipolar logic.

### Ordering Information

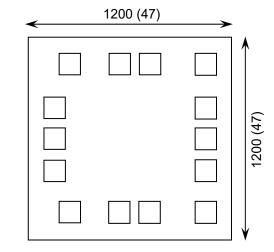
The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see

<u>54ACT32</u>

### Die Dimensions in µm (mils)



### Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

### Mechanical Specification

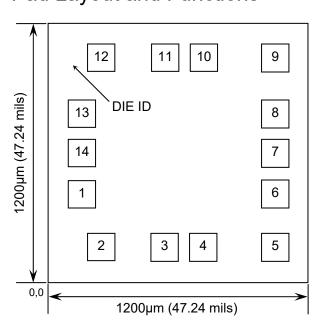
Die Size (Unsawn)	1200 x 1200 47 x 47	µm mils	
Minimum Bond Pad Size	120 x 120 4.72 x 4.72	µm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	µm mils	
Top Metal Composition	Al 1%Si 1.1µ	m	
Back Metal Composition	N/A – Bare Si		





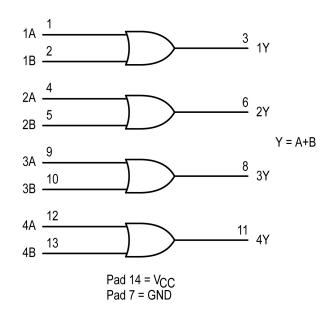
# Pad Layout and Functions

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PAD	FUNCTION	COORDIN	ATES (µm)
FAD	TONCTION	X	Y
1	1A	100	350
2	1B	150	100
3	1Y	480	100
4	2A	660	100
5	2B	990	100
6	2Y	990	350
7	GND	990	540
8	3Y	990	720
9	3A	990	980
10	3B	660	980
11	4Y	480	980
12	4A	150	980
13	4B	100	720
14	V <sub>cc</sub>	100	540
CON	INECT CHIP BA	CK TO V <sub>CC</sub> OI	R FLOAT

### Logic Diagram



### **Function Table**

INP	UTS	OUTPUT				
Α	В	Y				
L	L	L				
L	Н	Н				
Н	L	Н				
Н	Н	Н				
H = High level (steady state)						
L = L	ow level	(steady state)				





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### Absolute Maximum Ratings<sup>1</sup>

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V <sub>CC</sub>	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> +0.5	V
DC Output Voltage (Referenced to GND)	V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> +0.5	V
DC Input Current	I <sub>IN</sub>	±20	mA
DC Output Current, per pad	I <sub>OUT</sub>	±50	mA
DC Supply Current, V <sub>CC</sub> or GND, per pad	I <sub>CC</sub>	±50	mA
Power Dissipation in Still Air <sup>2</sup>	PD	750	mW
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°C

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

## Recommended Operating Conditions<sup>3</sup> (Voltages Referenced to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS
DC Supply Voltage	V <sub>cc</sub>	4.5	5.5	V
DC Input or Output Voltage	V <sub>IN</sub> ,V <sub>OUT</sub>	0	V <sub>CC</sub>	V
Operating Temperature Range	TJ	-40	+85	°C
Output current - High	I <sub>ОН</sub>	-	-24	mA
Output current - Low	I <sub>OL</sub>	-	24	mA
Input Rise or Fall rate $V_{CC} = 4$	.5V Δt/ΔV	0	10	ns/V
( $V_{IN}$ from 0.8V to 2V) $V_{CC} = 5$	5.5V	0	8	115/V

3. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{IN}$  and  $V_{OUT}$  should be constrained to the range GND  $\leq$  ( $V_{IN}$  or  $V_{OUT}$ )  $\leq$   $V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

#### DC Electrical Characteristics (Voltages referenced to GND)

PARAMETER	SYMBOL		LIMITS			UNITS	
	UTIMBUL	•00	CONDITIONO	25°C	85°C	FULL RANGE <sup>4</sup>	
Minimum High-Level	VIH	4.5V	$V_{OUT}$ = 0.1V or $V_{CC}$	2	2	2	V
Input Voltage	VН	5.5V	-0.1V	2	2	2	v
Maximum Low-Level Input Voltage	VIL	4.5V	$V_{OUT}$ = 0.1V or $V_{CC}$	0.8	0.8	0.8	V
	VIL	5.5V	-0.1V	0.8	0.8	0.8	v
Minimum High-Level Output Voltage		4.5V	Ι <sub>ουτ</sub> = -50μΑ	4.4	4.4	4.4	V
	Vau	5.5V	1001 – -30µA	5.4	5.4	5.4	V
	V OH	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^{5}$	3.86	3.76	3.76	V
	5.	5.5V	I <sub>ОН</sub> = -24mA	4.86	4.76	4.76	V

**4.**  $-40^{\circ}C \le T_{J} \le +85^{\circ}C$ 





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### DC Electrical Characteristics Continued (Voltages referenced to GND)

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PARAMETER	SYMBOL	L V <sub>cc</sub> CONDITIONS		LIMITS			UNITS
	OTMEOL	VCC	CONDITIONO	25°C	85°C	FULL RANGE <sup>4</sup>	UNITO
		4.5V	Ι <sub>ουτ</sub> = 50μΑ	0.1	0.1	0.1	V
Maximum Low-Level	V <sub>OL</sub>	5.5V	ι <sub>ουτ</sub> – 30μΑ	0.1	0.1	0.1	v
Output Voltage	V OL	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^{5}$	0.36	0.44	0.44	V
		5.5V I <sub>OL</sub> = 24mA	0.36	0.44	0.44	V	
Maximum Input Leakage Current	I <sub>IN</sub>	5.5V	$V_{IN} = V_{CC}$ or GND	±0.1	±1.0	±1.0	μA
Additional Maximum I <sub>cc</sub> / Input	ΔI <sub>CCT</sub>	5.5V	$V_{IN} = V_{CC} - 2.1V$	1	1.5	1.5	mA
Minimum Dynamic	I <sub>OLD</sub>	5.5V	V <sub>OLD</sub> = 1.65V Max	-	75	75	
Output Current <sup>6</sup>	I <sub>OHD</sub>	5.5V	V <sub>OHD</sub> = 3.85V Min	-	-75	-75	mA
Maximum Quiescent Supply Leakage Current	I <sub>CC</sub>	5.5V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	4	40	40	μA

5. All outputs loaded; thresholds on input associated with output under test. 6. Maximum test duration 2.0 ms, one output loaded at a time.

# AC Electrical Characteristics<sup>7</sup> ( $V_{cc} = 5.0V \pm 0.5V$ )

PARAMETER SYMB	SYMBOL	V <sub>cc</sub>	CONDITIONS		LIMIT	S	UNITS
		01111202	•	CONDITIONO	25°C	85°C	FULL RANGE <sup>4</sup>
Maximum PropagationtplHDelay, Input A or B totoOutput Y (Figure 1)tphL	5.0V	0 F0 F	9	10	10		
	t <sub>PHL</sub>	5.0V	C <sub>L</sub> = 50pF	9	10	10	ns

### Capacitance<sup>7</sup>

PARAMETER	SYMBOL	V <sub>cc</sub>	CONDITIONS	TYPICAL	UNITS
Maximum Input Capacitance	C <sub>IN</sub>	5.0V	T <sub>J</sub> = 25°C	4.5	pF
Power Dissipation Capacitance	C <sub>PD</sub>	5.0V	$T_{J} = 25^{\circ}C,$ $C_{L} = 50pF$	20	pF

7. Not production tested in die form, characterized by chip design and tested in package.





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### Switching Waveform

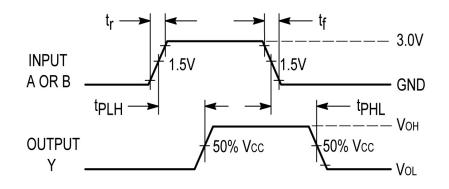
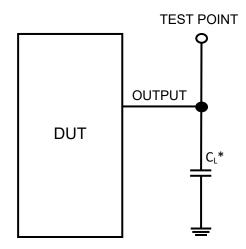


Figure 1 – Propagation Delay

#### **Test Circuit**



\* Includes all probe and jig capacitance

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